

Silicon Diffused Power Transistor

BU2530AW

GENERAL DESCRIPTION

New generation, high-voltage, high-speed switching npn transistor in a plastic envelope intended for use in horizontal deflection circuits of large screen colour television receivers up to 32 kHz.

QUICK REFERENCE DATA

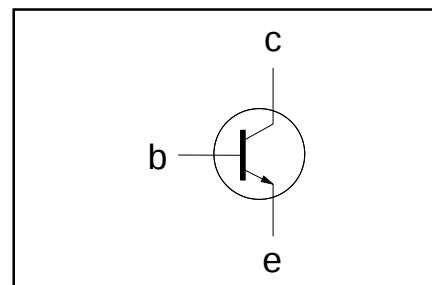
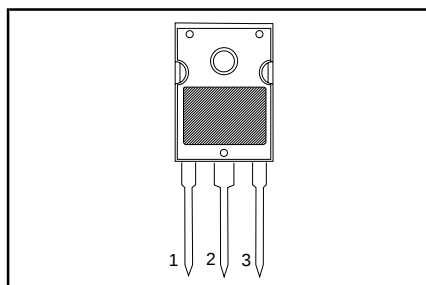
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	800	V
I_C	Collector current (DC)		-	16	A
I_{CM}	Collector current peak value		-	40	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25\text{ }^{\circ}\text{C}$	-	125	W
V_{CESat}	Collector-emitter saturation voltage	$I_C = 9.0\text{ A}; I_B = 1.64\text{ A}$	-	5.0	V
I_{Csat}	Collector saturation current		9	-	A
t_s	Storage time	$I_{Csat} = 9.0\text{ A}; I_{B(end)} = 1.3\text{ A}$	3.5	4.5	μs

PINNING - SOT429

PIN CONFIGURATION

SYMBOL

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	800	V
I_C	Collector current (DC)		-	16	A
I_{CM}	Collector current peak value		-	40	A
I_B	Base current (DC)		-	10	A
I_{BM}	Base current peak value		-	15	A
$-I_{B(AV)}$	Reverse base current	average over any 20 ms period	-	200	mA
$-I_{BM}$	Reverse base current peak value ¹		-	10	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25\text{ }^{\circ}\text{C}$	-	125	W
T_{stg}	Storage temperature		-55	150	$^{\circ}\text{C}$
T_j	Junction temperature		-	150	$^{\circ}\text{C}$

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Junction to mounting base	-	-	1.0	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	45	-	K/W

¹ Turn-off current.

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STATIC CHARACTERISTICS

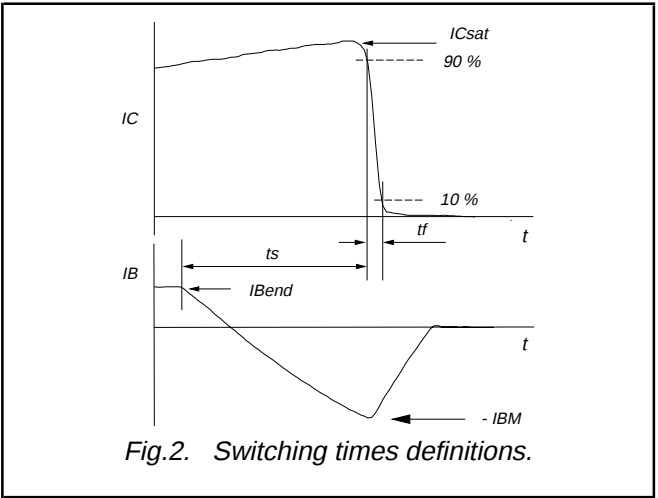
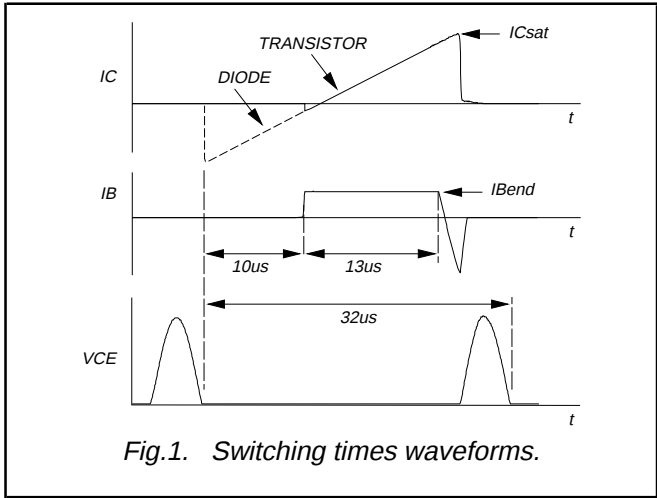
T_{mb} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CES}	Collector cut-off current ²	V _{BE} = 0 V; V _{CE} = V _{CESMmax}	-	-	1.0	mA
I _{CES}		V _{BE} = 0 V; V _{CE} = V _{CESMmax} T _J = 125 °C	-	-	2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} = 7.5 V; I _C = 0 A	-	-	1.0	mA
BV _{EBO}	Base-emitter breakdown voltage	I _B = 1 mA	7.5	14	-	V
V _{CEsat}	Collector-emitter saturation voltage	I _C = 9.0 A; I _B = 1.64 A	-	-	5.0	V
V _{BESat}	Base-emitter saturation voltage	I _C = 9.0 A; I _B = 1.64 A	0.825	0.91	1.0	V
h _{FE}	DC current gain	I _C = 1 A; V _{CE} = 5 V	9	17	27	
h _{FE}		I _C = 9 A; V _{CE} = 5 V	5.5	8	10	

DYNAMIC CHARACTERISTICS

T_{mb} = 25 °C unless otherwise specified

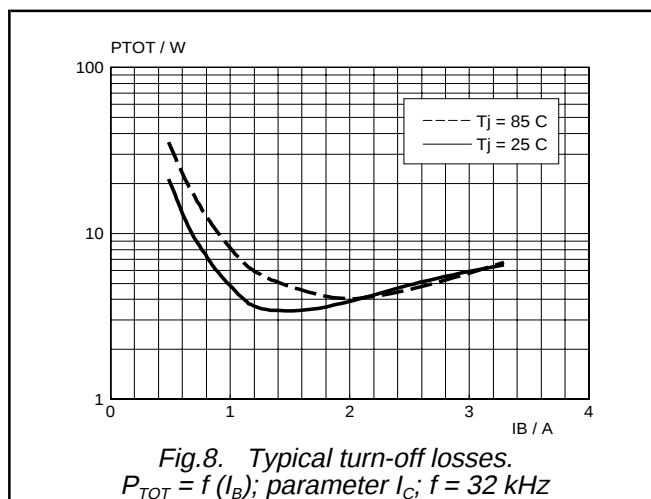
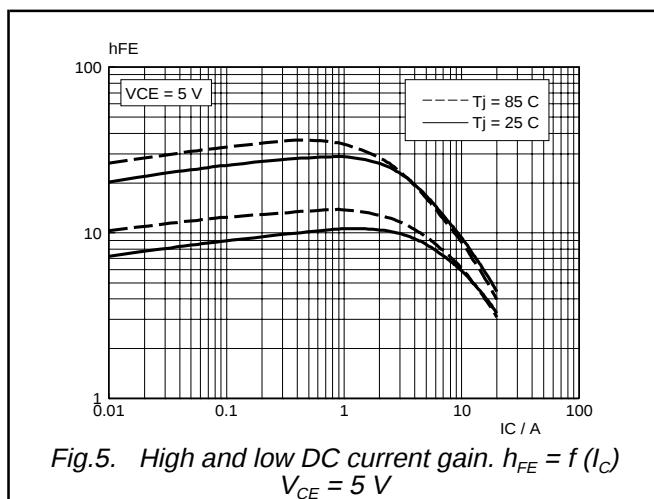
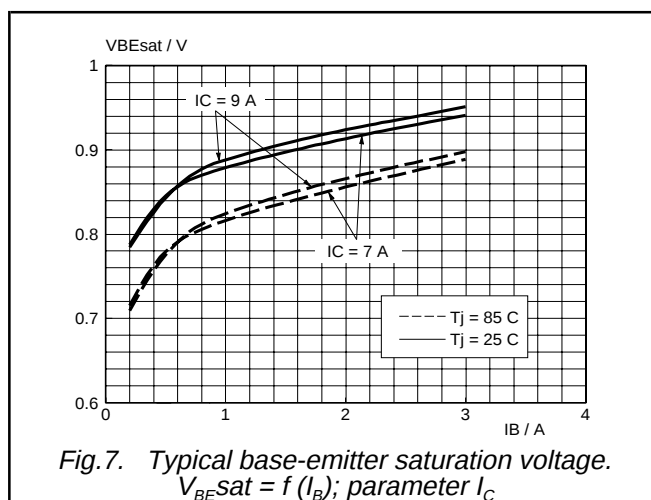
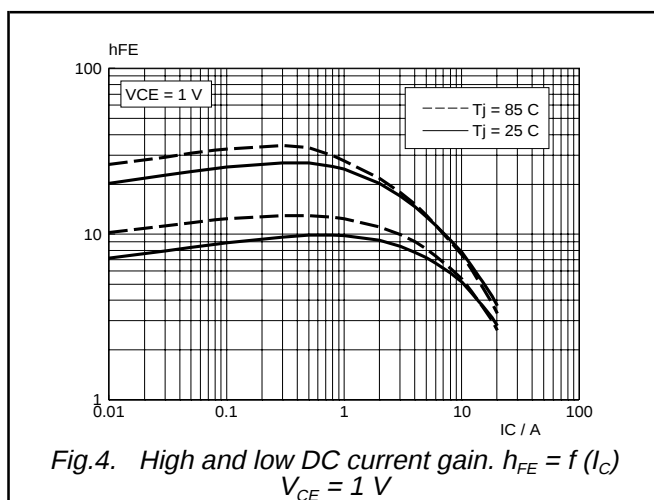
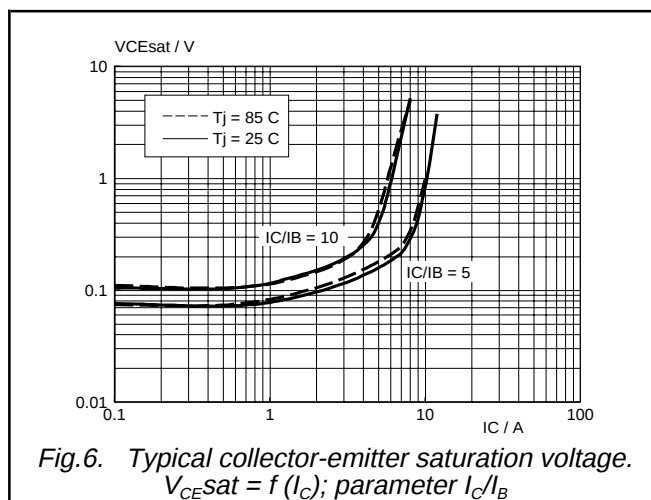
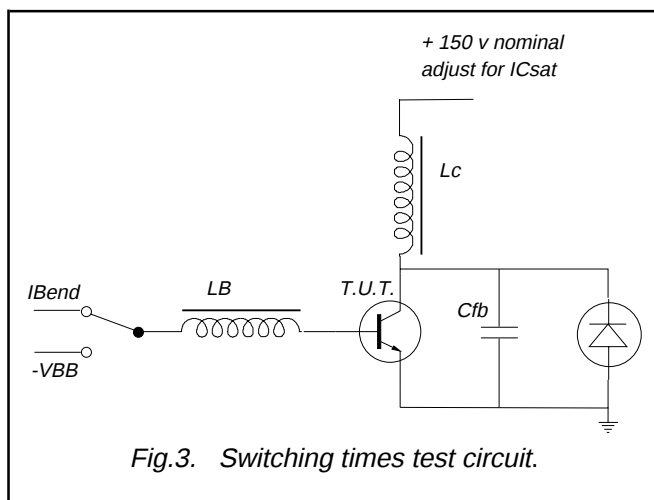
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (32 kHz line deflection dynamic test circuit).	I _{Csat} = 9.0 A; L _C = 200 μH; C _{fb} = 13 nF; V _{CC} = 138 V; I _{B(end)} = 1.3 A; -I _{BM} = 4.5 A; -V _{BB} = 4 V; L _B = 1 μH			
t _s	Turn-off storage time		3.5	4.5	μs
t _f	Turn-off fall time		0.14	0.25	μs



2 Measured with half sine-wave voltage (curve tracer).

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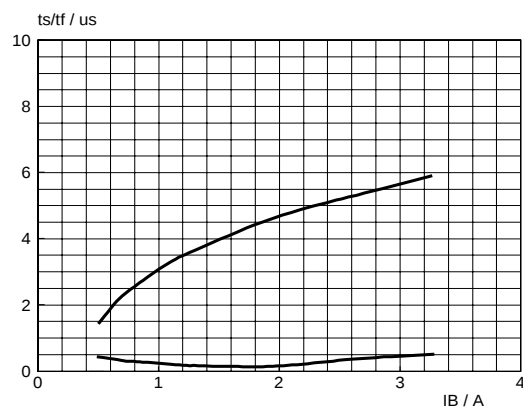


Fig.9. Typical collector storage and fall time.
 $t_s = f(I_B)$; $t_f = f(I_B)$; parameter I_C ; $T_j = 85^\circ\text{C}$; $f = 32\text{ kHz}$

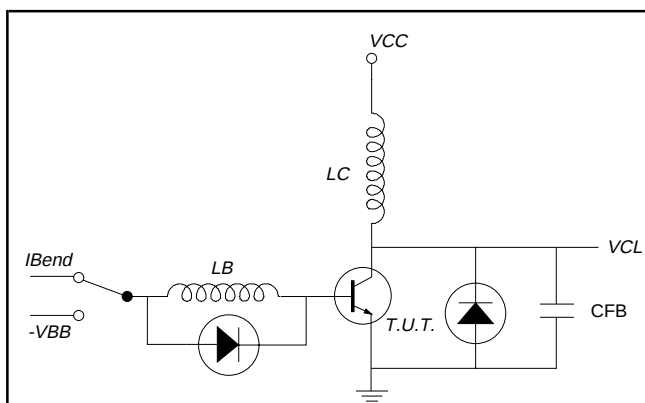


Fig.12. Test Circuit RBSOA. $V_{CC} = 150\text{ V}$;
 $-V_{BB} = 1 - 5\text{ V}$;
 $L_C = 1.5\text{ mH}$; $V_{CL} = 1450\text{ V}$; $L_B = 1 - 3\text{ }\mu\text{H}$;
 $C_{FB} = 1 - 10\text{ nF}$; $I_{B(\text{end})} = 1.3 - 2.6\text{ A}$

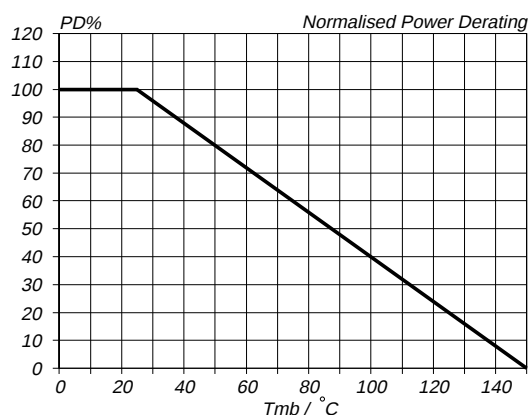


Fig.10. Normalised power dissipation.
 $PD\% = 100 \cdot P_D / P_{D 25^\circ\text{C}} = f(T_{mb})$

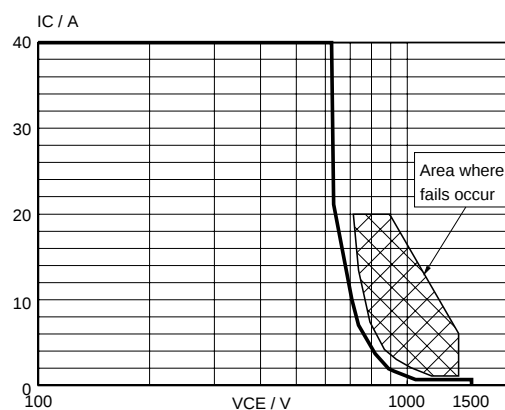


Fig.13. Reverse bias safe operating area. $T_j \leq T_{j\text{max}}$

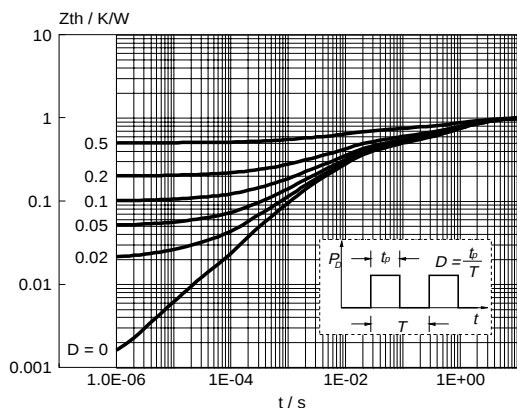
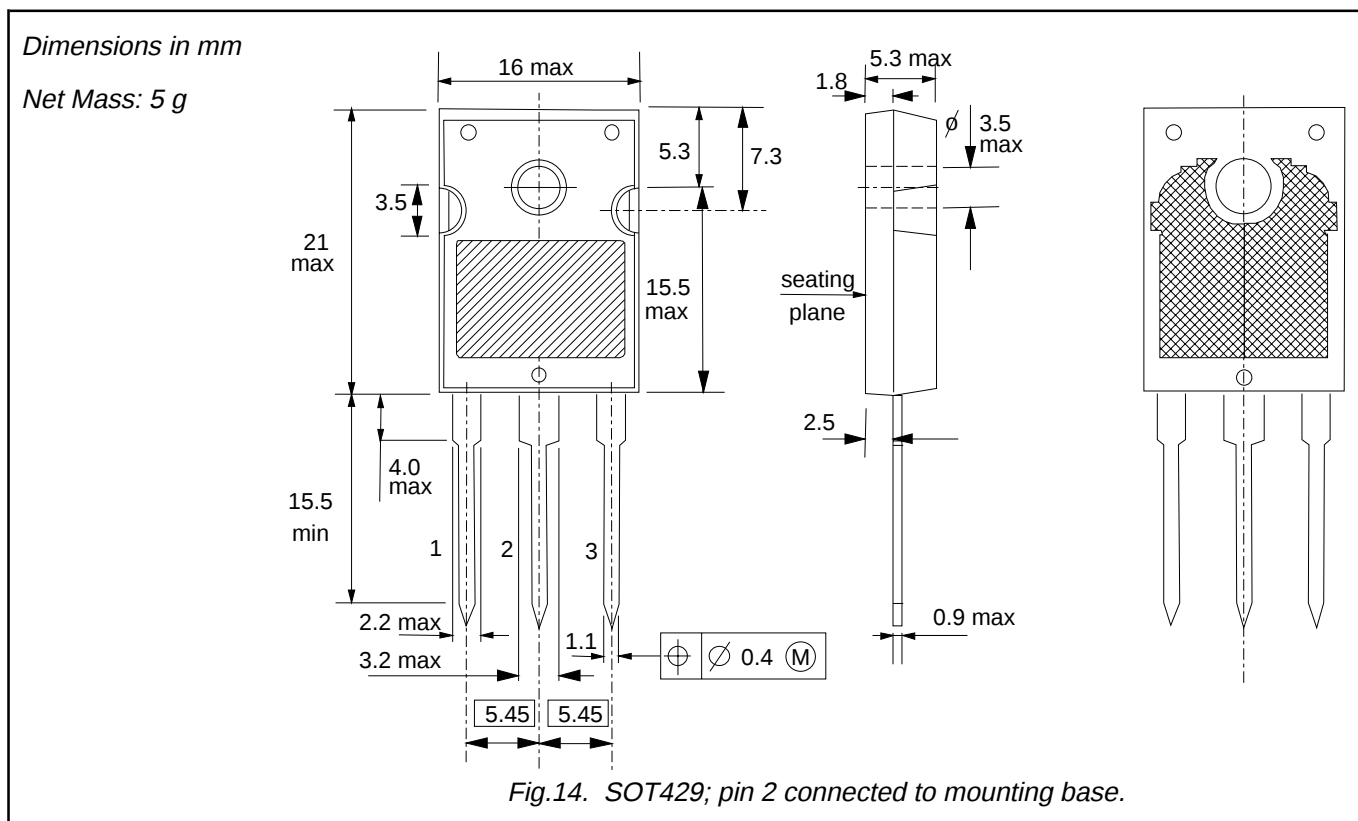


Fig.11. Transient thermal impedance.
 $Z_{th j-mb} = f(t)$; parameter $D = t_p / T$

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MECHANICAL DATA



Notes

1. Refer to mounting instructions for SOT429 envelope.
2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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